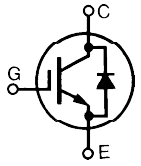
IXYS

XPT™ 650V IGBT GenX4™ w/ Diode

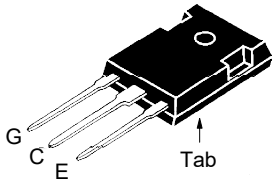
IXXH80N65B4D1

V_{CES} = 650V
I_{C110} = 80A
$V_{CE(sat)}$ ≤ 2.1V
$t_{fi(typ)}$ = 53ns

Extreme Light Punch Through
IGBT for 5-30 kHz Switching



TO-247



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 175°C	650	V
V_{CGR}	T_J = 25°C to 175°C, R_{GE} = 1MΩ	650	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	180	A
I_{C110}	T_C = 110°C	80	A
I_{F110}	T_C = 110°C	65	A
I_{CM}	T_C = 25°C, 1ms	430	A
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 3Ω Clamped Inductive Load	I_{CM} = 160 @$V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	V_{GE} = 15V, V_{CE} = 360V, T_J = 150°C R_G = 82Ω, Non Repetitive	10	µs
P_C	T_C = 25°C	625	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	°C
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250µA, V_{GE} = 0V	650			V
$V_{GE(th)}$	I_C = 250µA, V_{CE} = V_{GE}	4.0		6.5	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			25	µA
	T_J = 150°C			2	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 80A, V_{GE} = 15V, Note 1		1.65	2.10	V
	T_J = 150°C		2.00		V

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Diode
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

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Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	25	42		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		3860		pF
C_{oes}			395		pF
C_{res}			58		pF
$Q_{g(on)}$	I_C = 80A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		120		nC
Q_{ge}			32		nC
Q_{gc}			46		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		26		ns
t_{ri}	I_C = 80A, V_{GE} = 15V		100		ns
E_{on}	V_{CE} = 400V, R_G = 3Ω		3.36		mJ
$t_{d(off)}$	Note 2		112		ns
t_{fi}			53		ns
E_{off}			1.83		mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		23		ns
t_{ri}	I_C = 80A, V_{GE} = 15V		102		ns
E_{on}	V_{CE} = 400V, R_G = 3Ω		5.50		mJ
$t_{d(off)}$	Note 2		128		ns
t_{fi}			94		ns
E_{off}			2.70		mJ
R_{thJC}				0.24	°C/W
R_{thCS}			0.21		°C/W

Reverse Diode (FRED)

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 50A, V_{GE} = 0V, Note 1			2.5	V
	T_J = 150°C		1.35		V
I_{RM}	I_F = 50A, V_{GE} = 0V, $-di_F/dt$ = 500A/µs,		26		A
t_{rr}	V_R = 400V		140		ns
R_{thJC}				0.47	°C/W

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

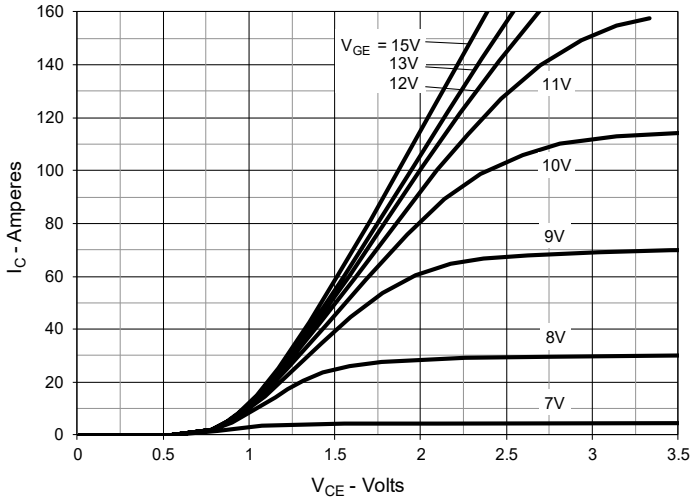


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

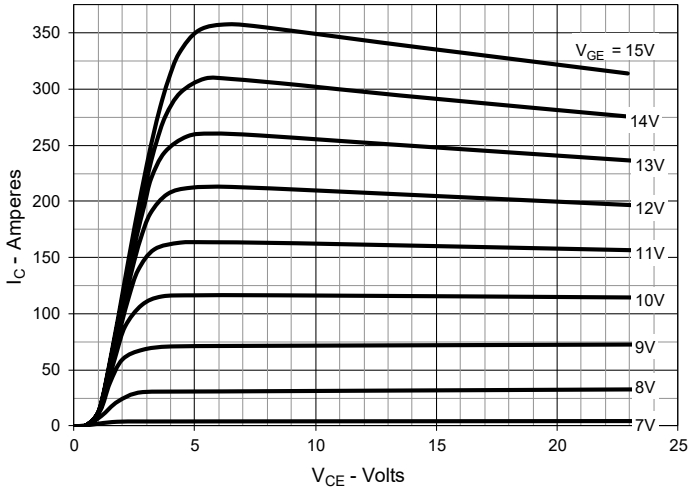


Fig. 3. Output Characteristics @ T_J = 150ºC

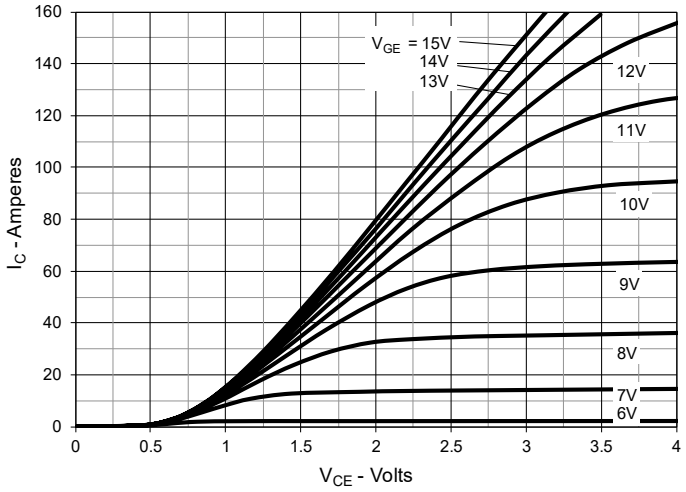


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

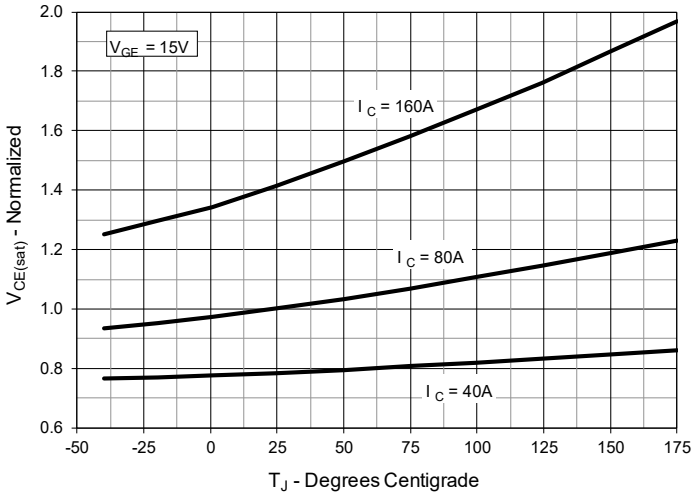


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

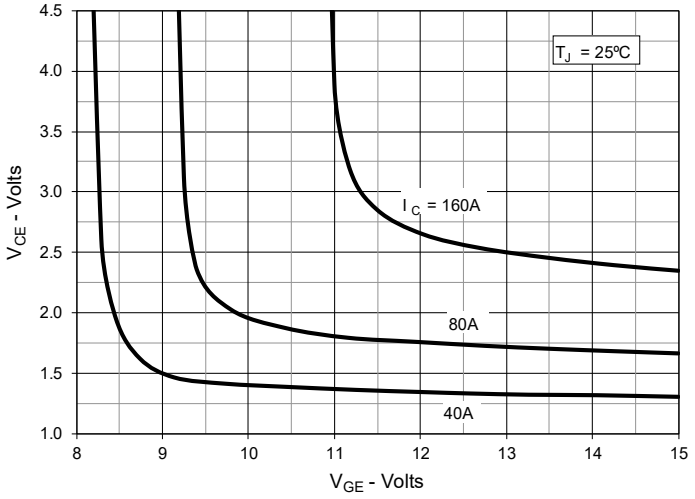
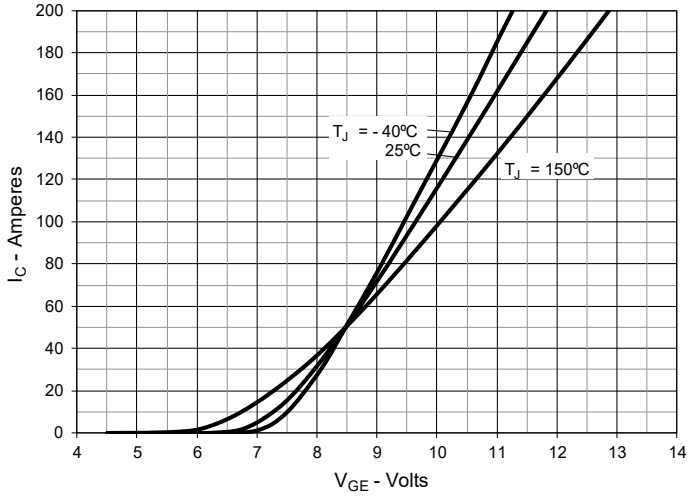


Fig. 6. Input Admittance



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Fig. 7. Transconductance

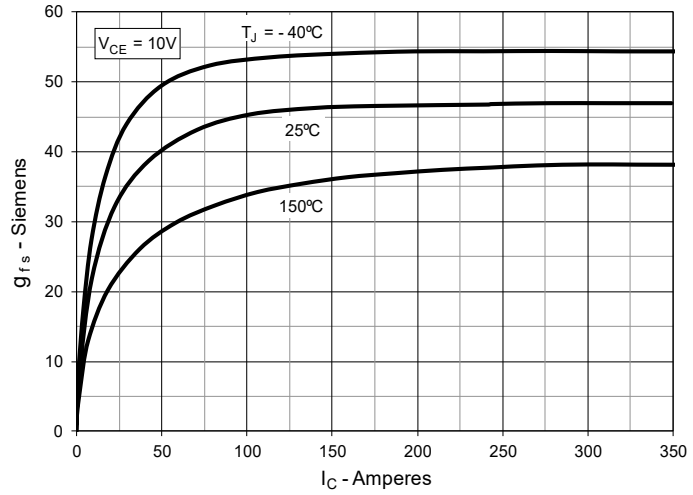


Fig. 8. Gate Charge

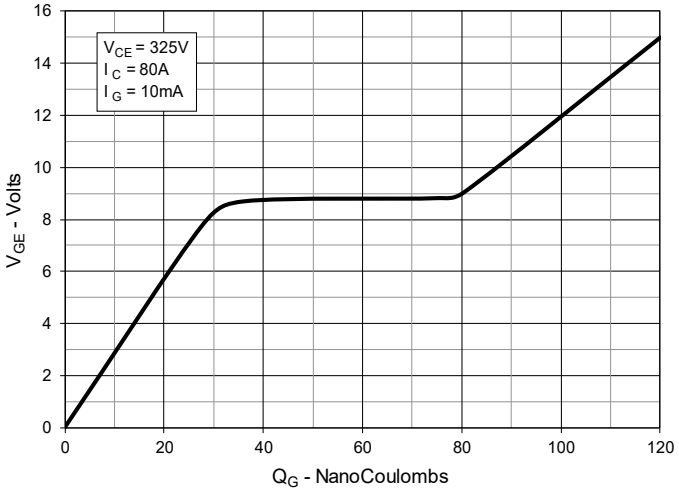


Fig. 9. Capacitance

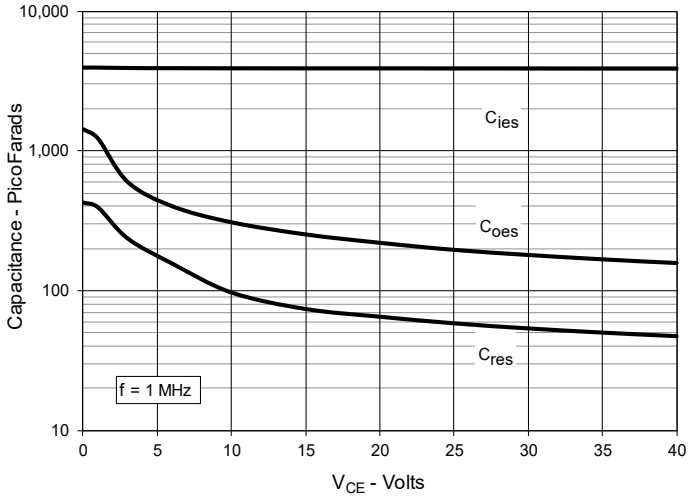


Fig. 10. Reverse-Bias Safe Operating Area

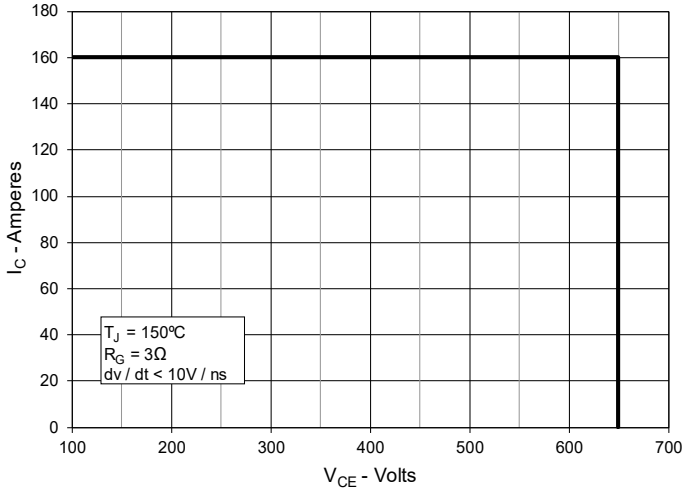
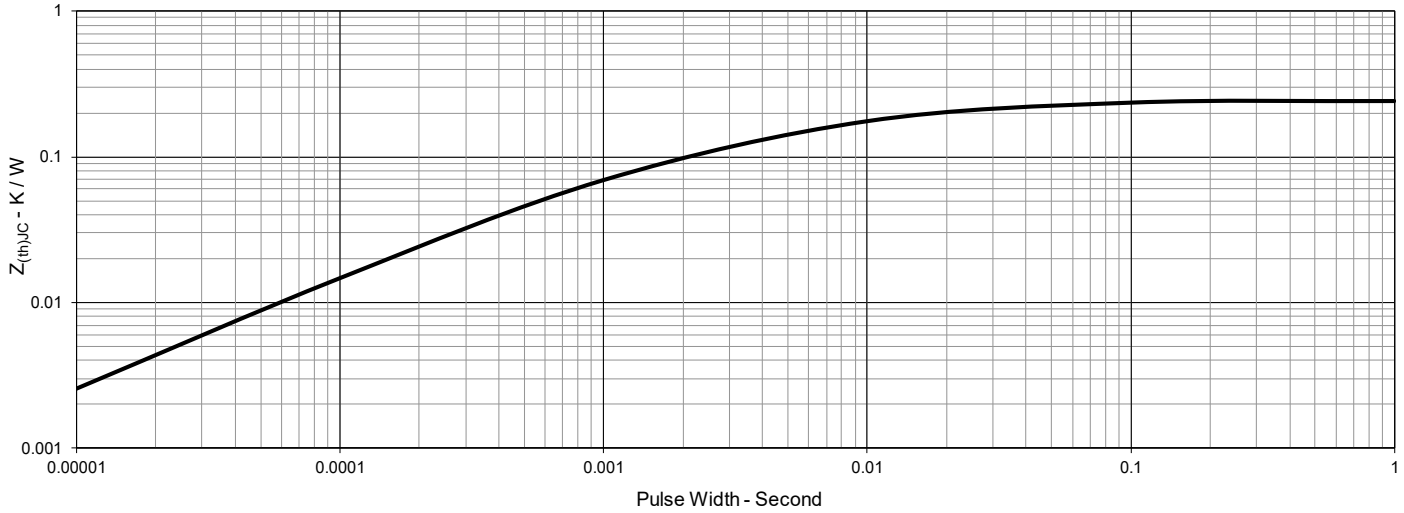


Fig. 11. Maximum Transient Thermal Impedance (IGBT)



Littelfuse reserves the right to change limits, test conditions, and dimensions.

Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

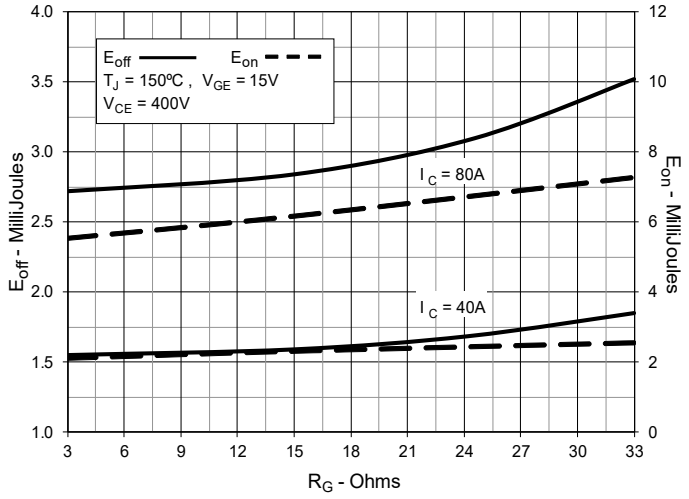


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

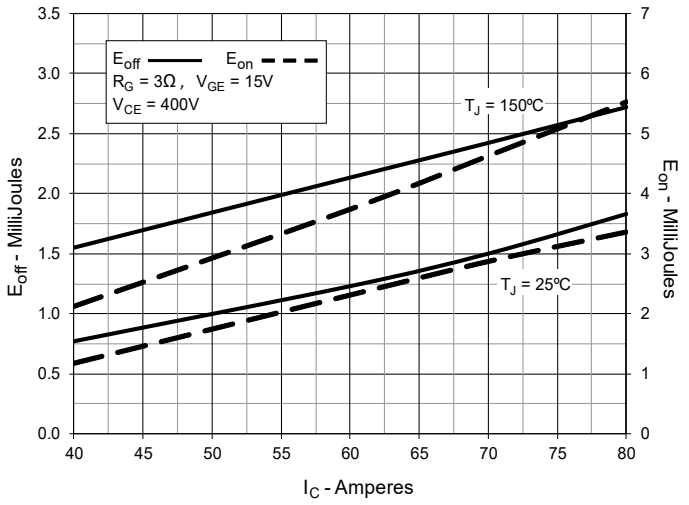


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

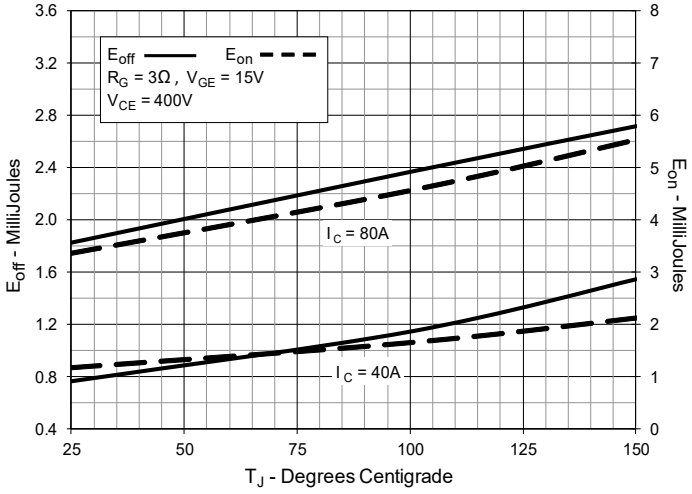


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

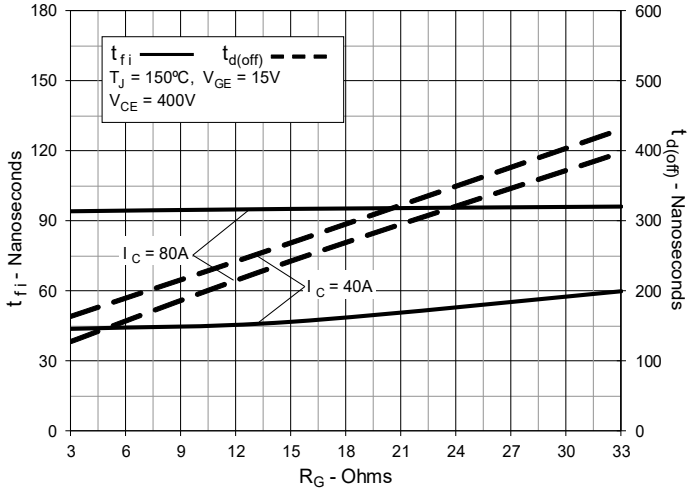


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

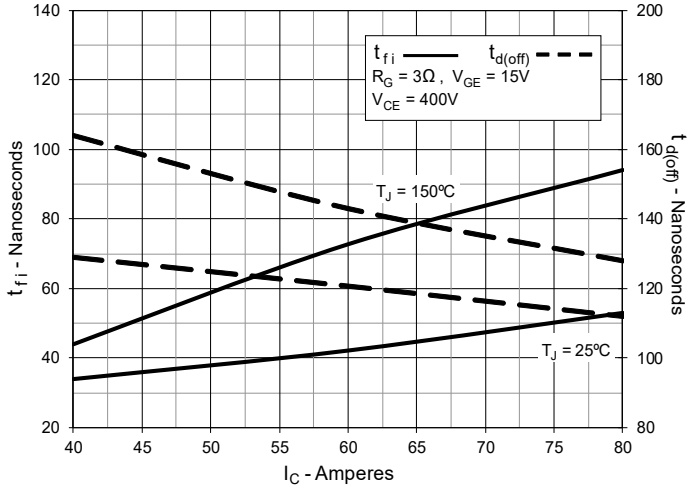
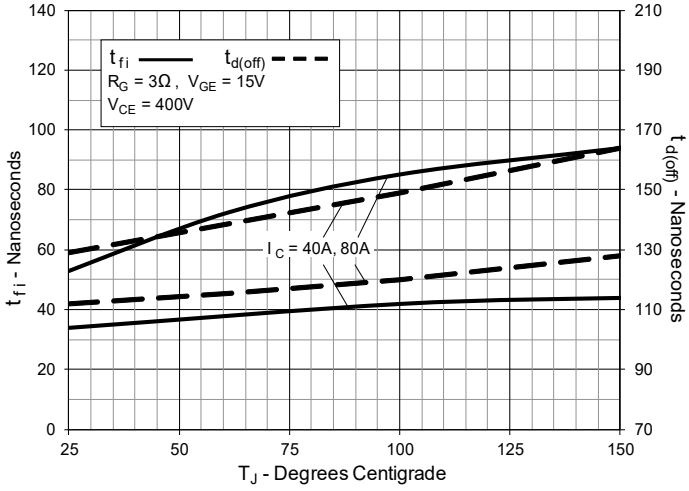


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

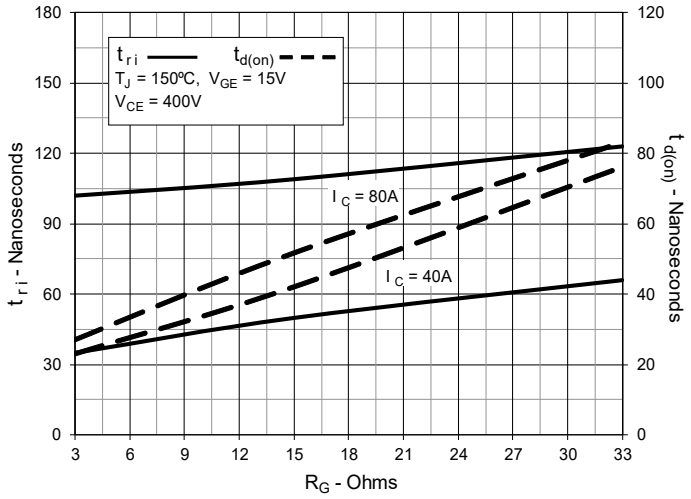


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

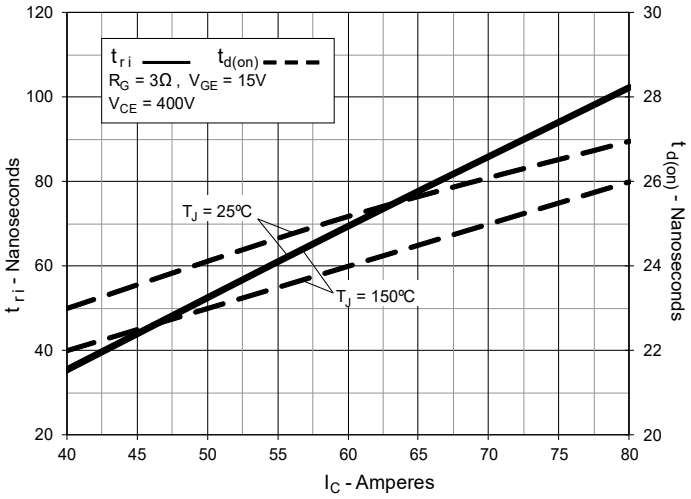


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

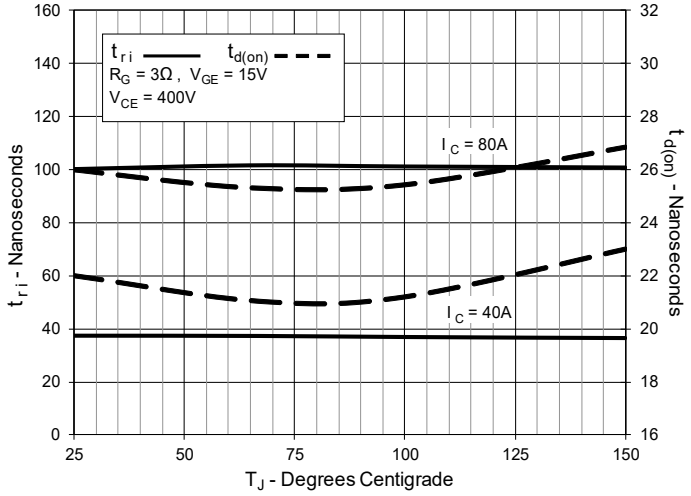


Fig. 21. Diode Forward Characteristics

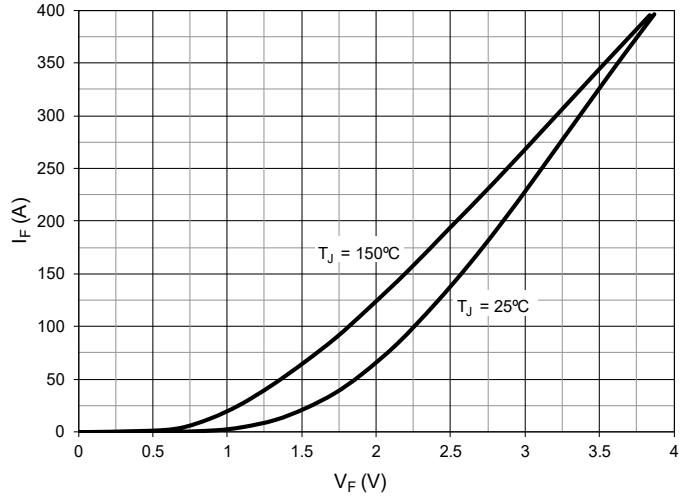


Fig. 22. Reverse Recovery Charge vs. -di_F/dt

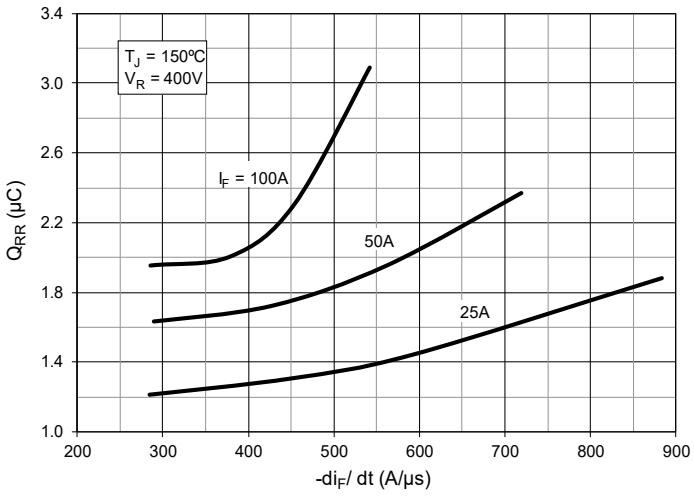


Fig. 23 Reverse Recovery Current vs. -di_F/dt

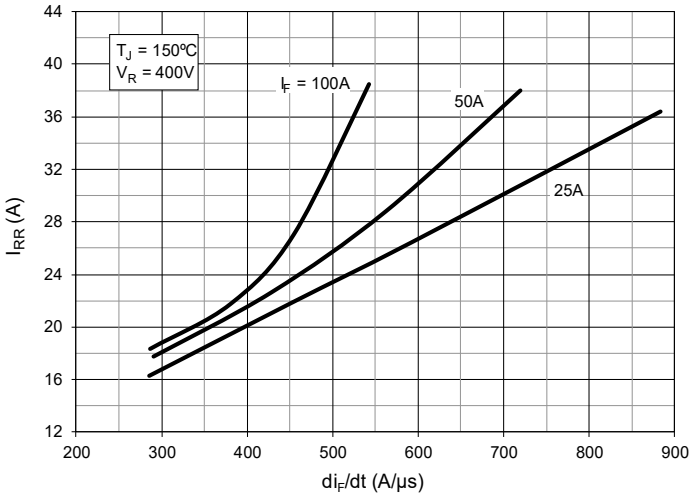


Fig. 24. Reverse Recovery Time vs. -di_F/dt

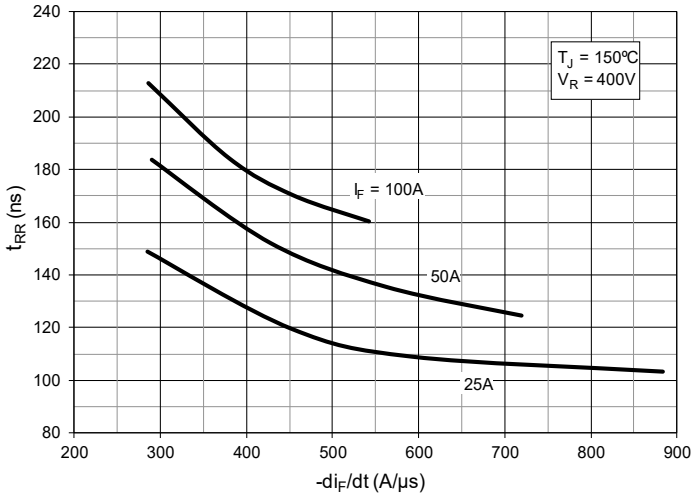


Fig. 25. Dynamic Parameters Q_{RR}, I_{RR} vs. Junction Temperature

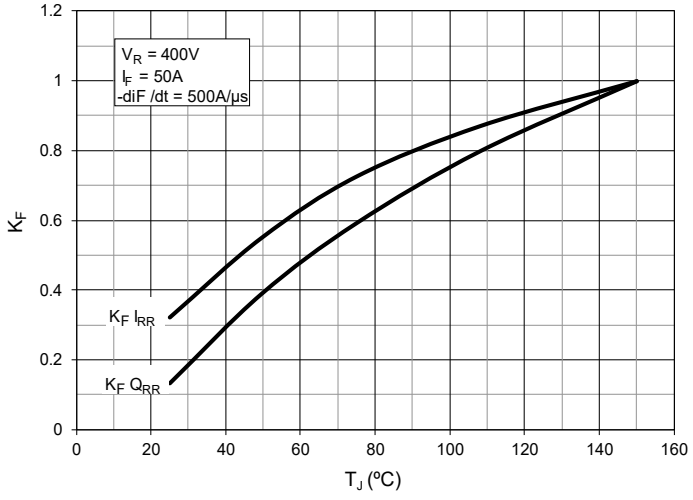
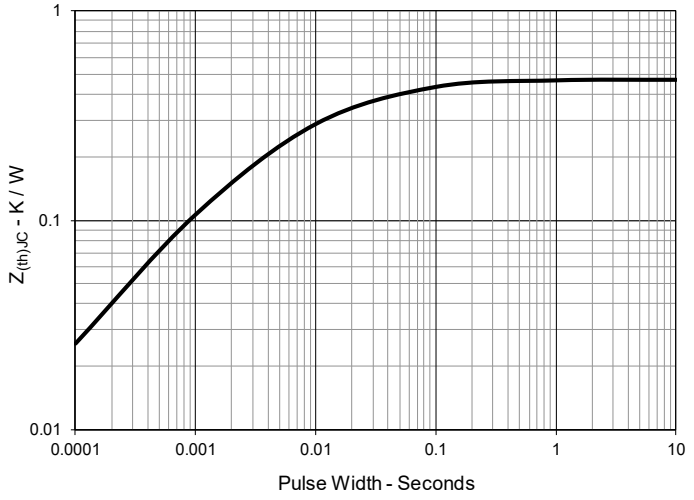
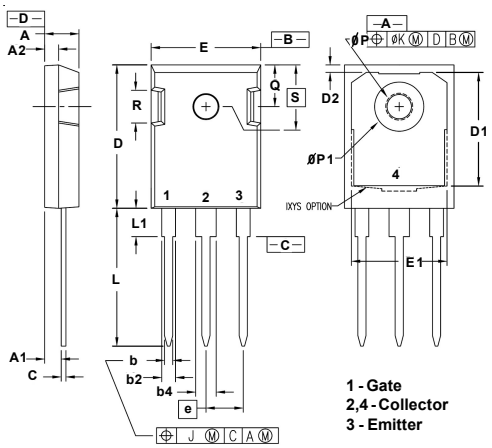


Fig. 26. Maximum Transient Thermal Impedance (Diode)



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TO-247 Outline



1 - Gate
2,4 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

Littelfuse reserves the right to change limits, test conditions, and dimensions.



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